

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|--|-----------------------------------|----------------------|
| 1 | BRS | L1 | 1070 | 257/412 | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:14 |
| 2 | BRS | L2 | 341 | (MOS or metal near oxide near transistor) and decoupling near capacitor | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:25 |
| 3 | BRS | L3 | 0 | L2 and (platinum near silicate or PtSi) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:19 |
| 4 | BRS | L4 | 2 | L2 and (platinum and silicate or PtSi) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:21 |
| 5 | BRS | L5 | 810 | (platinum near silicate or PtSi) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:21 |
| 6 | BRS | L6 | 1 | (platinum near silicate or PtSi)and (decoupling near capacitor) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:22 |
| 7 | BRS | L7 | 4 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (flat near band) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:30 |
| 8 | BRS | L8 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near level near substrate) | USPAT ; JPO; DERWE NT | 2001/10/2 4 16:31 |

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|----|------|-----|------|--|-----------------------|------------------|
| 9 | BRS | L9 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (modify near dopant near | USPAT ; JPO; DERWE NT | 2001/10/24 16:32 |
| 10 | BRS | L10 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (change near dopant near | USPAT ; JPO; DERWE NT | 2001/10/24 16:32 |
| 11 | BRS | L11 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near level) | USPAT ; JPO; DERWE NT | 2001/10/24 16:32 |
| 12 | BRS | L12 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate near dopant near level) | USPAT ; JPO; DERWE NT | 2001/10/24 16:33 |
| 13 | BRS | L13 | 3 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate near | USPAT ; JPO; DERWE NT | 2001/10/24 16:34 |
| 14 | BRS | L14 | 5 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near concentration) | USPAT ; JPO; DERWE NT | 2001/10/24 16:40 |
| 15 | BRS | L15 | 5 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate) and (dopant near | USPAT ; JPO; DERWE NT | 2001/10/24 16:40 |
| 16 | BRS | L16 | 0 | (MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate) near (dopant near | USPAT ; JPO; DERWE NT | 2001/10/24 16:41 |

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|----|------|-----|-------|---|-------------------------------|------------------|
| 17 | BRS | L17 | 0 | (decoupling near capacitor) and (substrate)near (dopant near concentration) | USPAT; JPO; DERWE NT | 2001/10/24 16:41 |
| 18 | BRS | L18 | 0 | (decoupling near capacitor) and (dopant near concentration near substrate) | USPAT; JPO; DERWE NT | 2001/10/24 16:41 |
| 19 | BRS | L19 | 6 | (decoupling near capacitor) and (dopant near concentration) | USPAT; JPO; DERWE NT | 2001/10/24 17:03 |
| 20 | BRS | L20 | 80234 | Chen CY.in. | USPAT; JPO; DERWE NT | 2001/10/24 17:04 |
| 21 | BRS | L21 | 10 | DHAKA.in. | USPAT; JPO; DERWE NT | 2001/10/24 17:06 |
| 22 | BRS | L22 | 9 | "3619735" | USPAT; JPO; DERWE NT | 2001/10/24 17:08 |
| 23 | BRS | L23 | 19 | "3769105" | USPAT; JPO; DERWE NT | 2001/10/24 17:12 |
| 24 | BRS | L24 | 44 | "4437139" | USPAT; JPO; DERWE NT | 2001/10/24 17:22 |